

BACK-END

TRANSISTOR

MOS-FET

IGBT

DIODE

THERMAL RESISTANCE TESTER 過渡熱抵抗測定器

DVFN240AT 200V
40A

- DVFN240AT is built-in model of a self-judgement and able to do forcing check for items of VDS, ID, and IM by GP-IB I/F.
- DVFN240ATは自己診断機能を内蔵しているモデルで、GP-IB I/FによりVDS、ID、IMの各アイテムの印加チェックを行うことができます。

MODEL		DVFN240AT
MEASUREMENT RANGE		
VBE1/VSD1/VGE1/VCE1/VF1		0000mV~9999mV
$\Delta V_{BE}/\Delta V_{SD}/\Delta V_{GE}/\Delta V_{CE}/\Delta V_{F}$		0000mV~1999mV
SETTING RANGE		
MEASURABLE DEVICES	NPN/PNP, N/P-MOS FET, N/P-DIODE, N/P-IGBT(GE), N/P-IGBT(CE)	
Vcb/Vds	1V~199V	
IE/ID	0.01A~39.9A	
IM	1mA~99mA	
POWER FORCING TIME(PT)	100 μ s~999ms	
DELAY TIME(DT)	10 μ s~999 μ s	
GATE LIMIT(GL)	1.0V~19.9V	
LOWER GATE(LG)/UPPER GATE(UG)	0000mV~1999mV	
BINNING		
OPEN/SHORT CHECK	VF1>4V...OPEN VF1<0.2V...SHORT	
BIN INDICATION	PASS, LOW, HIGH, AVAL, REJECT	
DIMENSIONS & WEIGHT		
MAIN UNIT	430(W) \times 700(D) \times 245(H)...50kg	
POWER UNIT	430(W) \times 700(D) \times 245(H)...60kg	
HEAD BOX	110(W) \times 200(D) \times 165(H)...2kg	



Forcing Power Range Diagram

